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FDP6030BL/FDB6030BL

N-Channel Logic Level PowerTrench® MOSFET

General Description

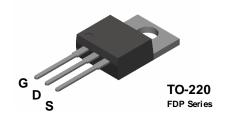
This N-Channel Logic Level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

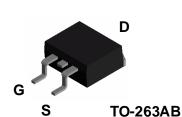
These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{\scriptscriptstyle DS(on)}$ specifications resulting in DC/DC power supply designs with higher overall efficiency.

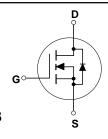
Features

- 40 A, 30 V. R $_{DS(ON)} = 0.018~\Omega~@~V_{GS} = 10~V$ R $_{DS(ON)} = 0.024~\Omega~@~V_{GS} = 4.5~V.$
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- High performance trench technology for extremely low $R_{\rm DS(ON)}$.
- 175°C maximum junction temperature rating.

FDB Series







Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	FDP6030BL	FDB6030BL	Units	
V _{DSS}	Drain-Source Voltage	30		V	
V_{GSS}	Gate-Source Voltage	±20		V	
I _D	Maximum Drain Current - Continuous (Note 1)	4	10	Α	
	- Pulsed	1	20		
P_D	Total Power Dissipation @ T _C = 25°C	60		W	
	Derate above 25°C	0.36		W/°C	
T_J , T_{STG}	Operating and Storage Junction Temperature Range	-65 to +175		°C	
Thermal Characteristics					
$R_{\theta_{JC}}$	Thermal Resistance, Junction-to-Case	2.5		°C/W	
$R_{\theta_{JA}}$	Thermal Resistance, Junction-to-Ambient	62.5		°C/W	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDB6030BL	FDB6030BL	13"	24mm	800
FDP6030BL	FDP6030BL	Tube	N/A	45

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
DRAIN-S	OURCE AVALANCHE RAT	INGS (Note 1)				•
W _{DSS}	Single Pulse Drain-Source Avalanche Energy	V _{DD} = 15 V, I _D = 40 A			150	mJ
I _{AR}	Maximum Drain-Source Avalnche	Current			40	Α
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	30			V
ΔBV _{DSS} ΔΤ.	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		23		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	μд
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Chara	acteristics (Note 1)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1	1.6	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_{.l}}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		-4.5		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A},$ $V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}, T_J = 125^{\circ}\text{C}$		0.015 0.021	0.018 0.030	Ω
1	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, I_D = 17 \text{ A}$	40	0.019	0.024	_
I _{D(on)}	Forward Transconductance	$V_{GS} = 10 \text{ V}, V_{DS} = 10 \text{ V}$ $V_{DS} = 5 \text{ V}, I_{D} = 20 \text{ A}$	40	30		A S
g _{FS}		V _{DS} = 3 V, I _D = 20 A	ļ	30		3
	Characteristics	Iv. 45 V V 6 V	ı	4400		
Ciss	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		1160		pF
Coss	Output Capacitance			250		pF
Crss	Reverse Transfer Capacitance			100		pF
t _{d(on)}	g Characteristics (Note 1) Turn-On Delay Time	V _{DD} = 15 V, I _D = 1 A,		9	17	ns
t _r	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$		11	20	ns
t _{d(off)}	Turn-Off Delay Time			23	37	ns
t _f	Turn-Off Fall Time			8	16	ns
Q _g	Total Gate Charge	V _{DS} = 15 V,		12	17	nC
Q_{gs}	Gate-Source Charge	$I_D = 20 \text{ A}, V_{GS} = 5 \text{ V}$		3.2		nC
Q_{gd}	Gate-Drain Charge			3.7		nC
	urce Diode Characteristics	and Maximum Patings				
<u>Diaiii-30</u> _s	Maximum Continuous Drain-Source				40	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 20 \text{ A}$ (Note 1)		0.95	1.2	V

Note: 1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Typical Characteristics

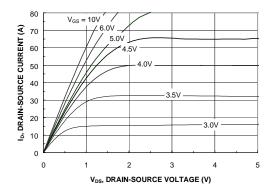


Figure 1. On-Region Characteristics.

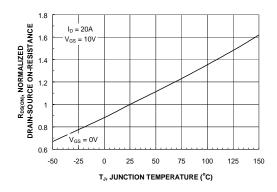


Figure 3. On-Resistance Variation with Temperature.

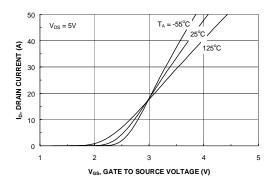


Figure 5. Transfer Characteristics.

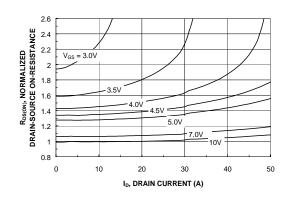


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

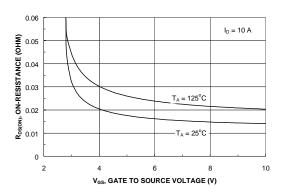


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

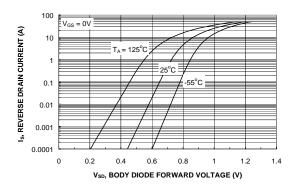
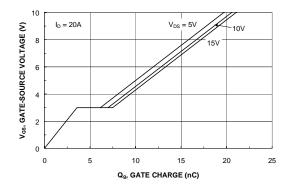


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)



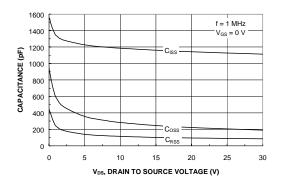
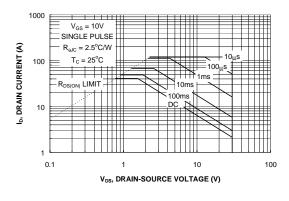


Figure 7. Gate-Charge Characteristics.





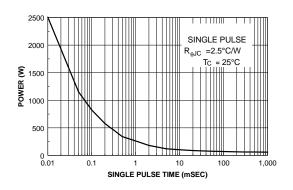


Figure 9. Maximum Safe Operating Area.



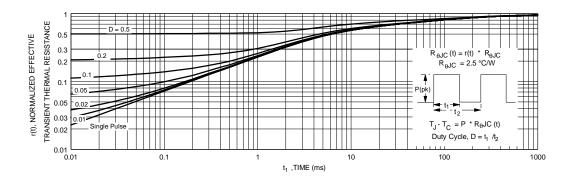


Figure 11. Transient Thermal Response Curve.

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